

Application No. 10/790,403
Filed: March 1, 2004
TC Art Unit: 2822
Confirmation No.: 1449

REMARKS

Claims 1-31 are currently pending. Claims 1-12 and claims 27-31 have been withdrawn from prosecution. Claims 13-23 have been allowed. Claims 24 and 25 stand rejected under 35 U.S.C. §103(a). Claim 26 is objected to but otherwise recites allowable subject matter.

Claims 1-12 and claims 27-31 have been canceled without prejudice. Accordingly, after entry of this amendment, the pending claims will be claims 13-26. Claim 24 has been amended to recite the subject matter in claim 26. Claim 26 has also been amended. In view of the above amendments, withdrawal of the grounds for rejection is respectfully requested.

35 U.S.C § 103(a) REJECTIONS

Claims 24 and 25 stand rejected under 35 U.S.C. § 103(a) as unpatentable over U.S. Patent Application Publication Number 2001/0032977 to Abe, et al. ("Abe") in view of U.S. Patent Number 6,566,233 to Yokokawa, et al. ("Yokokawa"). More specifically, per the Examiner, Abe otherwise anticipates the invention as claimed but for the steps of implanting hydrogen ions into the silicon body and performing a heating step to a cleaving temperature. The Examiner further asserts that Yokokawa teaches the implanting step and the heating step and, moreover, that it would have been obvious to combine the references. The Applicants respectfully traverse the grounds for rejection in view of the above amendments.

More specifically, claim 24 has been amended to include the allowable subject matter recited in claim 26. Accordingly, the

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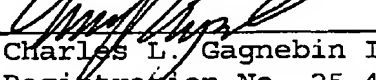
grounds for rejection with respect to claim 24 and dependent claim 25 are now moot.

Claim 26 has been amended to recite that step of providing a silicon epitaxial layer on the silicon fractured at the second hydrogen boundary includes first providing an n-type semiconductivity to the silicon, which is disclosed in the Specification between lines 1 and 6 on page 5. Neither of the references teaches, mentions or suggests providing a silicon epitaxial layer on the silicon fractured at the second hydrogen boundary or providing an n-type semiconductivity to the silicon before fracturing. Accordingly, claim 26 is believed to satisfy all of the requirements of 35 U.S.C. § 101, et seq. -- especially § 103(a) -- and is in condition for allowance.

The Examiner is encouraged to telephone the undersigned attorney to discuss any matter that would expedite allowance of the present application.

Respectfully submitted,

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